

# COMPASS

a FormFactor users' group conference



# Multi Sensor Metrology Tools for Hybrid Metrology in Wafer Manufacturing

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# Products

- Designed for full integration into automated production lines



**MicroProf® MHU**



**MicroProf® FS**



**MicroProf® FE/AP**

Fully automated systems with flexible sample handling

# Multi Sensor Metrology

- compact – multi-sensor – modular – standardized

## point sensors

- extremely flexible
- any scan range
- fast on large areas

## field of view sensors

- highest resolution
- large areas via stitching
- fast on small areas

## atomic force microscopy

- nm resolution
- large scan area
- easy handling

## film thickness sensors

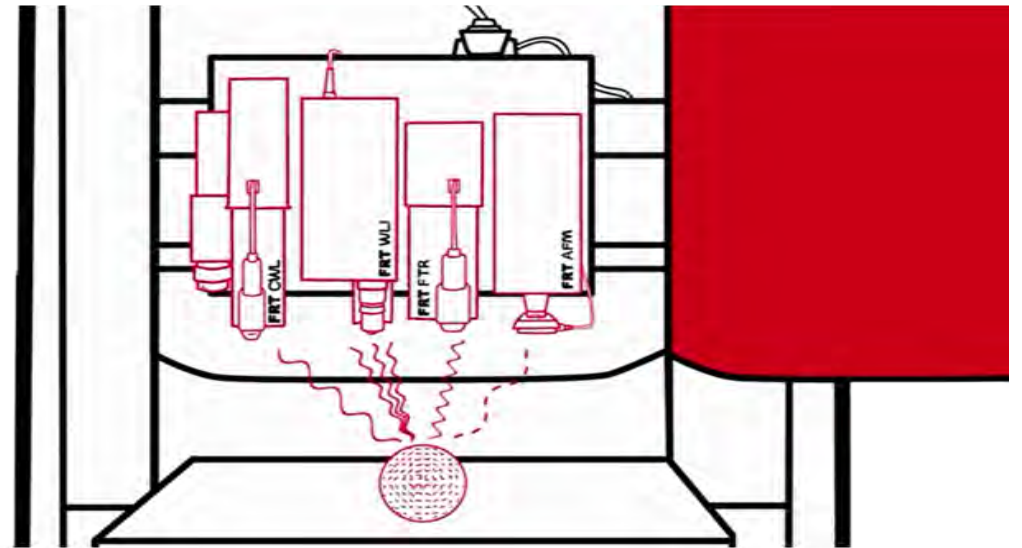
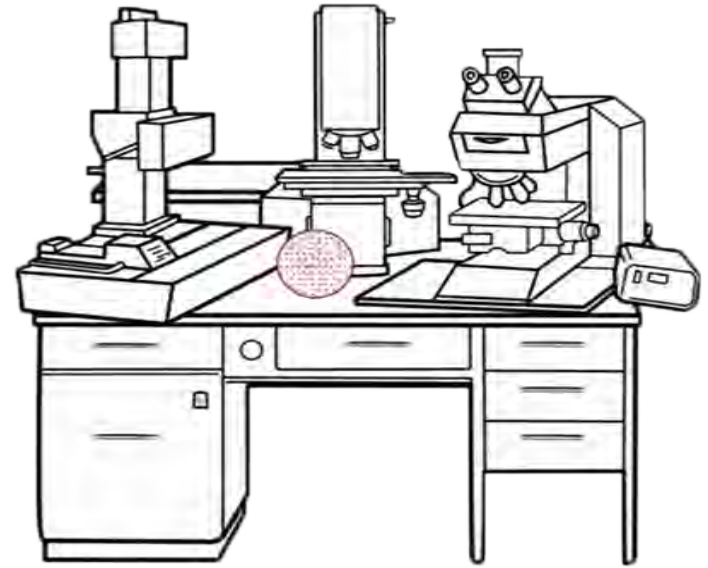
- highest resolution
- large measurement range
- measurement of multi layers





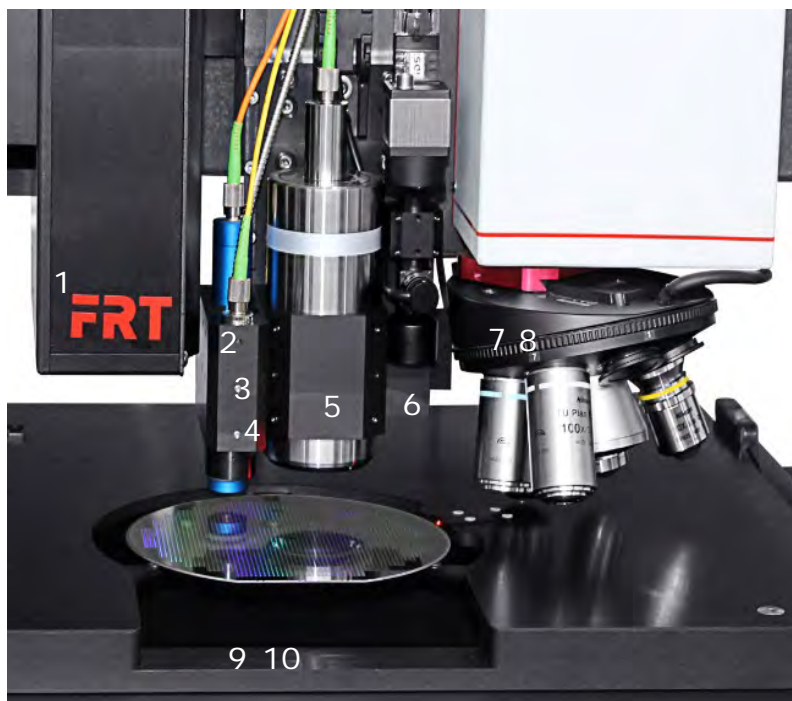
*topography*  
*profile*  
*roughness*  
*film thickness*

...



# Tool platform example

- All-in-one device due to unique multi sensor philosophy

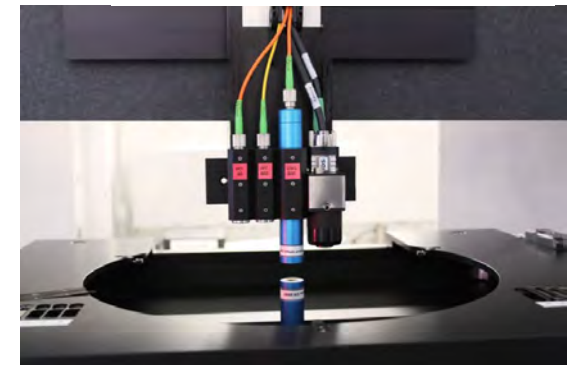


1. WLI PL (white light interferometer)
2. CWL 600  $\mu\text{m}$  (point sensor)
3. FTR (reflectometer layer thickness)
4. CWL FT (layer thickness sensor)
5. CWL 1 mm (point sensor)
6. High-resolution camera with pattern recognition
7. CFM DT (combi-sensor white light interferometer with 7x turret)
8. CFM DT (combi-sensor confocal microscope with 7x turret)
9. CWL 600  $\mu\text{m}$  (TTV point sensor), underside
10. FTR (reflectometer layer thickness), underside

Fully automated multi sensor and hybrid metrology arrangement – 10 sensors, 1 recipe

# MicroProf® Series - Wafer metrology tool for manufacturing

- 300 mm / 200 mm wafer stage
- multi sensor configuration
- hybrid metrology
- simultaneous measurement on both wafer sides
- multiple applications
- fully automated handling and integration
- fast and accurate measurement
- high repeatability and reproducibility
- fully SEMI compliant



# MicroProf® Series – Metrology for

die separation

bumps and pillars  
vias and trenches

FOWLP

MEMS cavities

edge trimming

advanced packaging  
2.5D / 3D IC



nanotopography

wafer thinning  
TTV, bow and warp

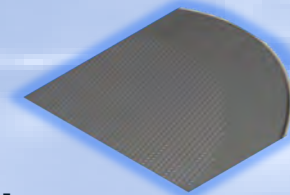
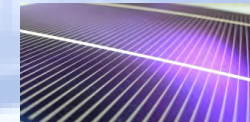
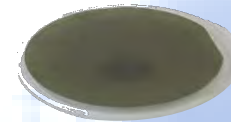
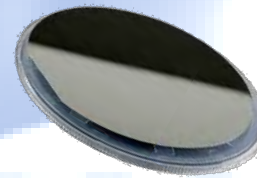
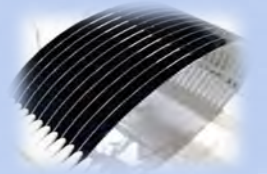
multilayer thickness  
polymers - PR/PI/BCB  
Oxides, Nitrides  
Silicon, RST, SOI  
Mold

**solutions for many process steps**



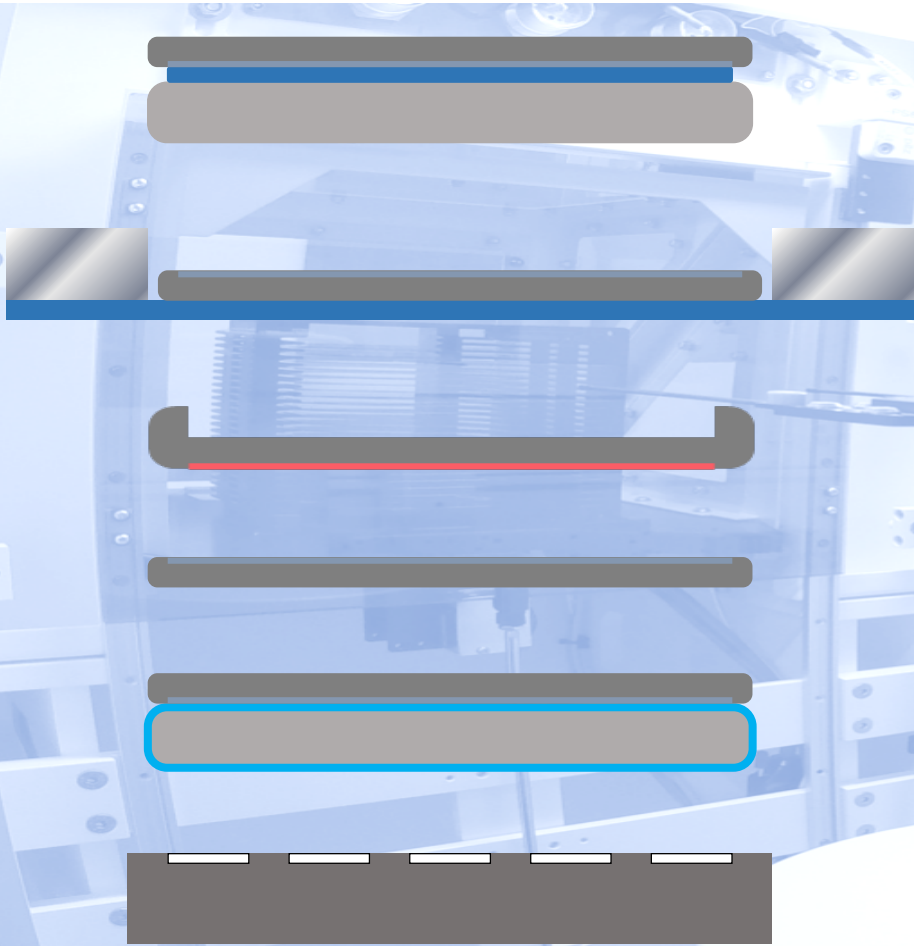
# MicroProf<sup>®</sup> Series – Measurement of

- semiconductors Si, Ge,...
- compound semiconductors GaAs, InP, SiC, GaN, ZnO...
- special substrates LiNbO<sub>3</sub>, DLC,...
- sapphire and glass wafer
- solar / PV mono-/poly-crystalline and amorphous Si
- lens wafers



**solutions for all materials**

# MicroProf® Series - Automated handling of



bonded wafers /wafer stack

wafer on tape in frame

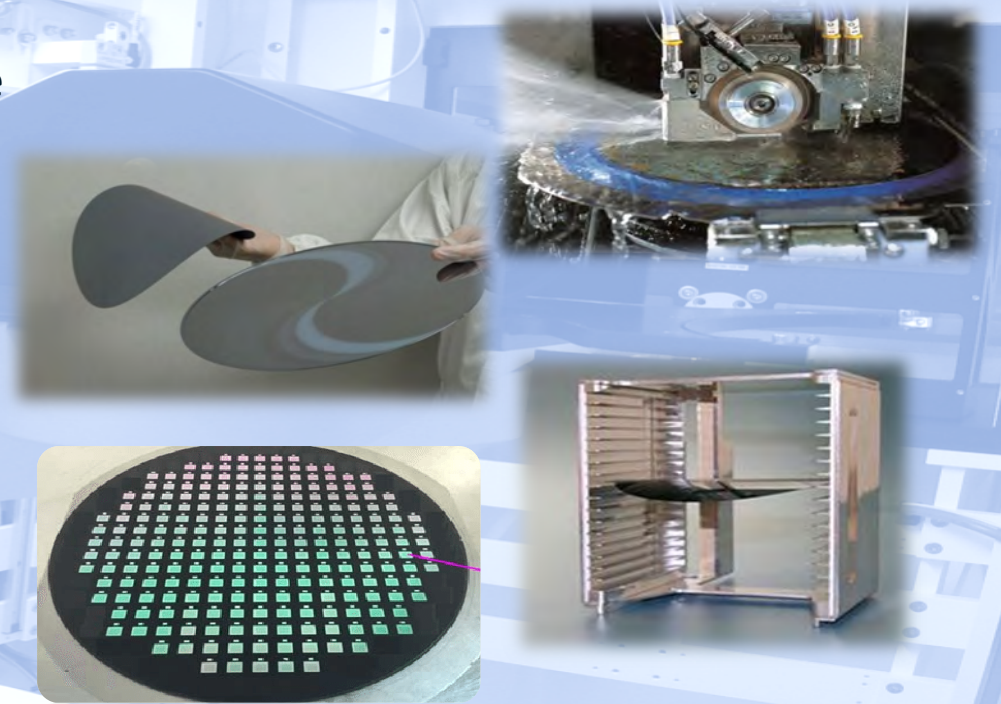
Taiko wafer

bare and  
thinned wafer > 50 µm

SOI wafer

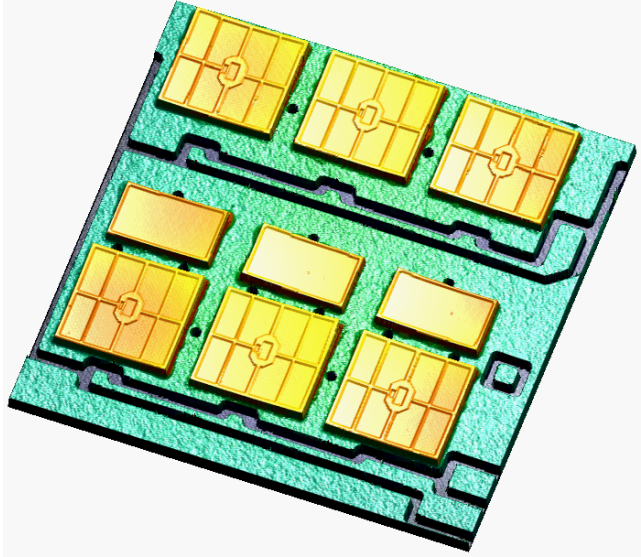
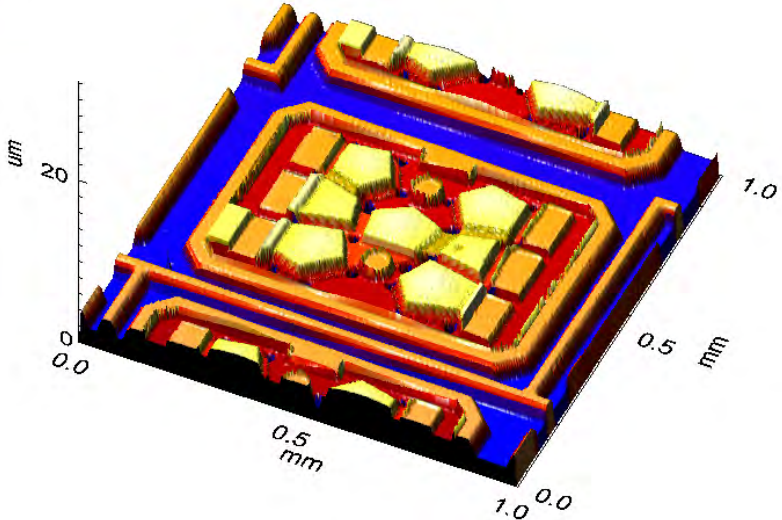
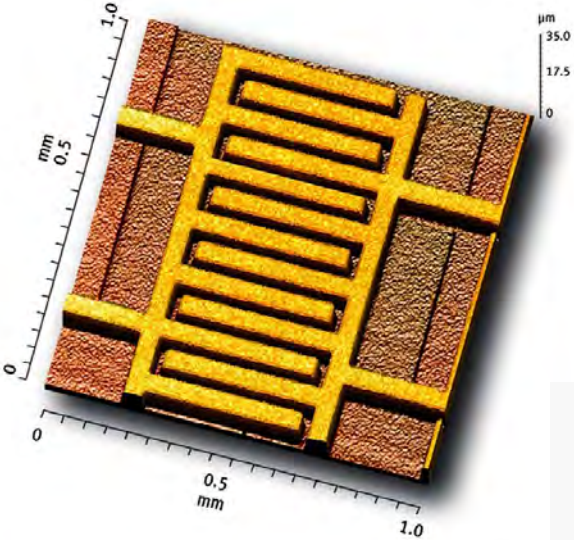
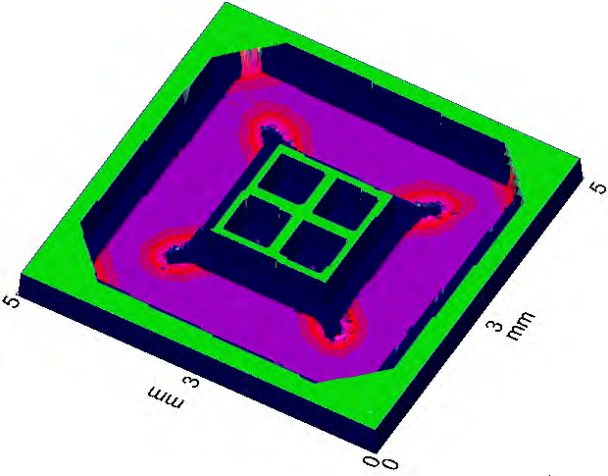
FO wafer

**solutions for all wafer types**



*photographs courtesy of DISCO HiTEC EUROPE GmbH,  
mechatronic systemtechnik gmbh and researchgate.net*

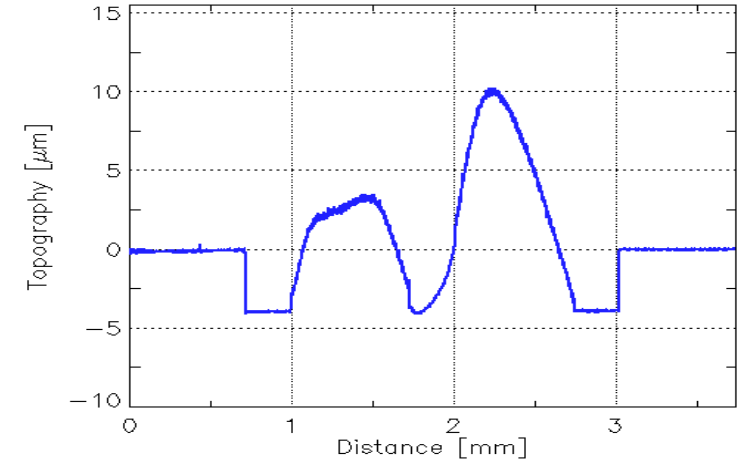
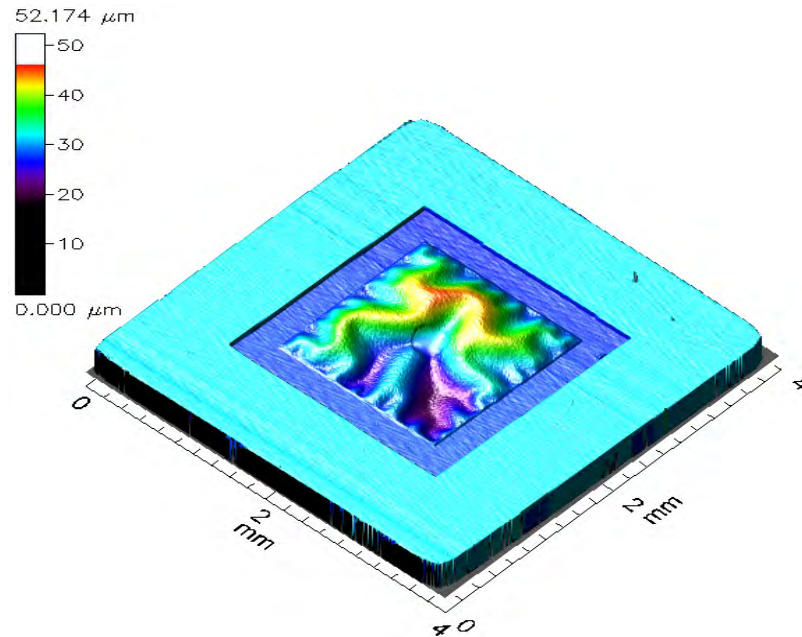
# Applications - MEMS and electronic components



# Application - MEMS

➤ evaluation of:

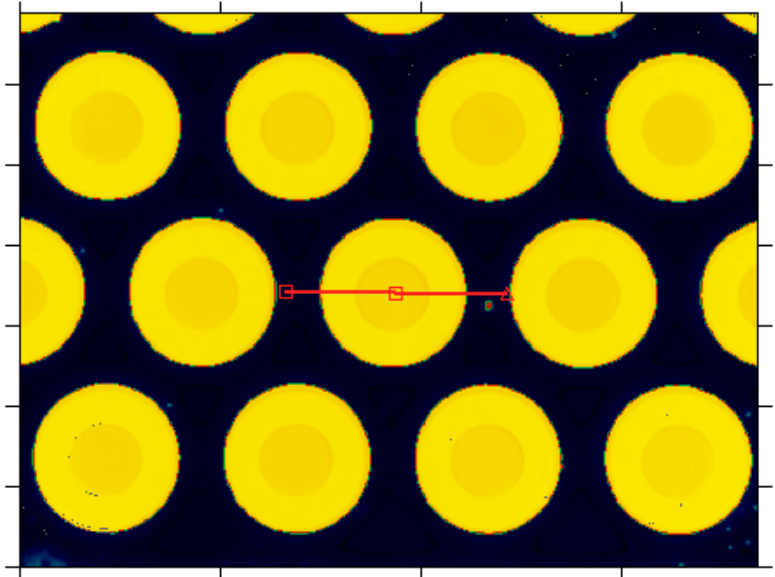
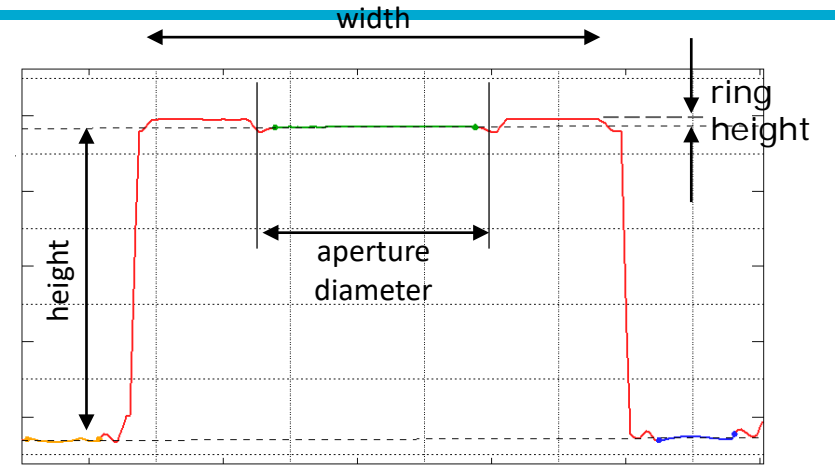
- profile and shape of total structure
- topography and radius



# Application - VCSELs

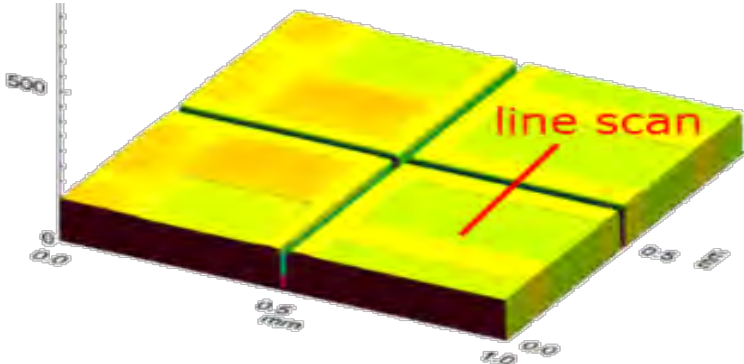
➤ evaluation of:

- height and width of total structure
- ring contact height to top of aperture
- aperture diameter

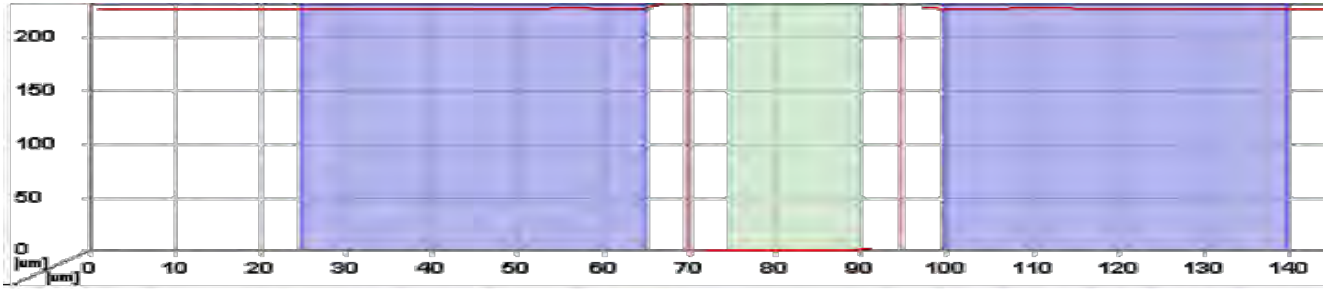


# Application - Trench ameasurement

- dynamic reproducibility of trench depths

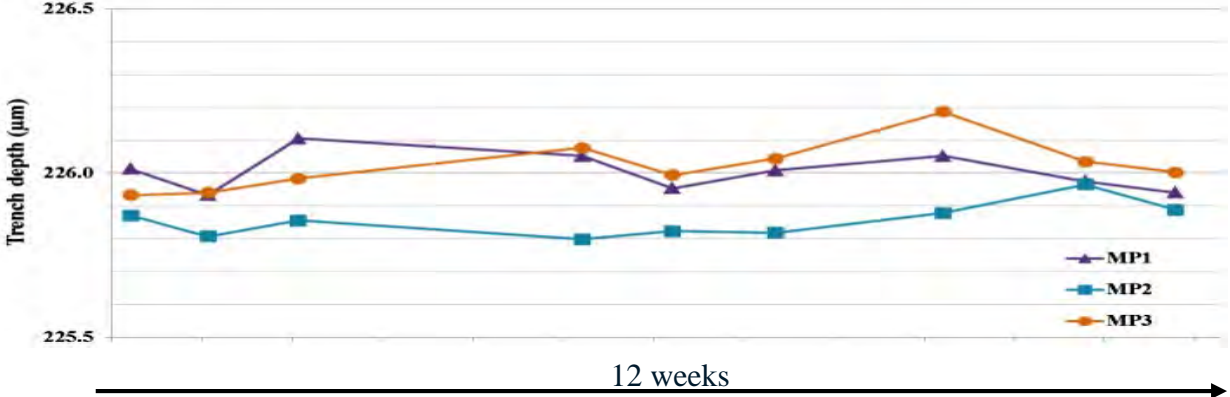


trench depth = 225.9  $\mu\text{m}$  / trench width = 24.8  $\mu\text{m}$



dynamic repeatability tests for 12 weeks:

$\sigma = 63 \text{ nm}$  (0.03 %)



ASMC2015: Optical step height and trench depth measurement , F.Heider et al. Infineon/FRT

# Application - Cavity measurement

➤ evaluation of:

- photo resists thickness over cavity  
area to control film thickness uniformity (coating might be influenced by bending of device wafer)
- thickness of device wafer and cavity depth
- topography of cavity area

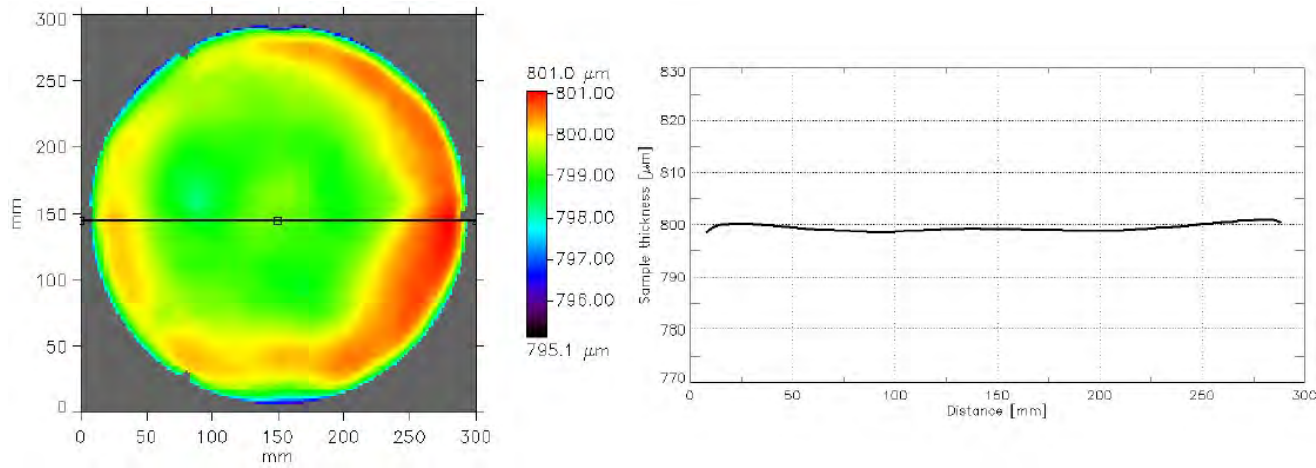


# Application

- Temporary carrier bonding



topography and TTV



dedicated sensors:  
2x CWL 600 µm  
(TTV setup)

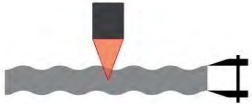


fast and reliable wafer thickness measurement



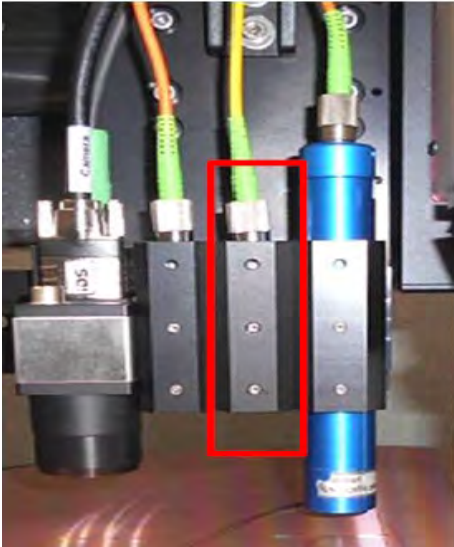
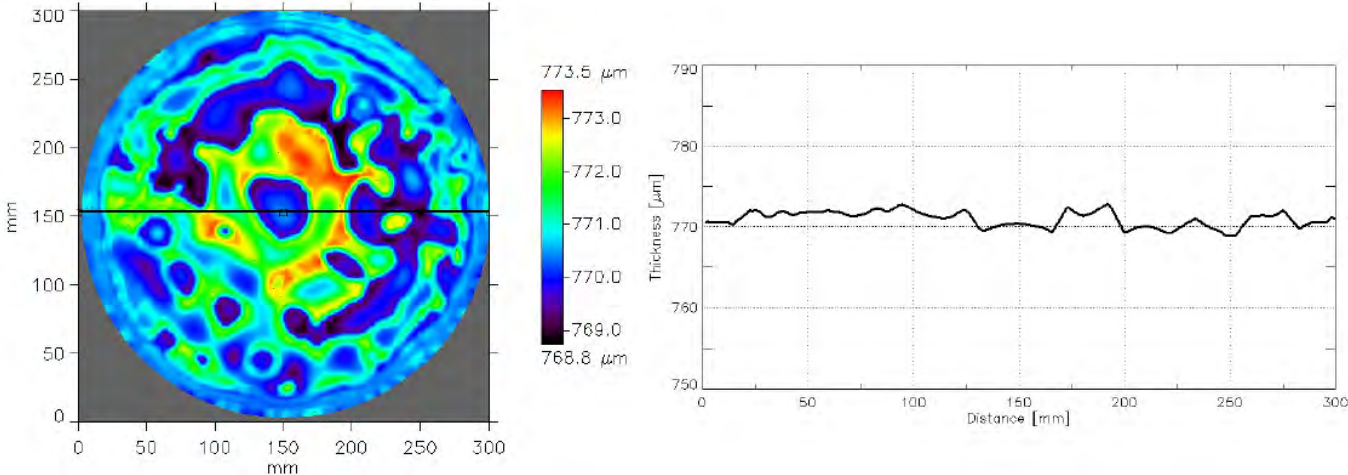
# Application

- Temporary carrier bonding



dedicated sensor:  
IRT 800

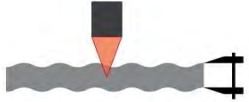
carrier wafer



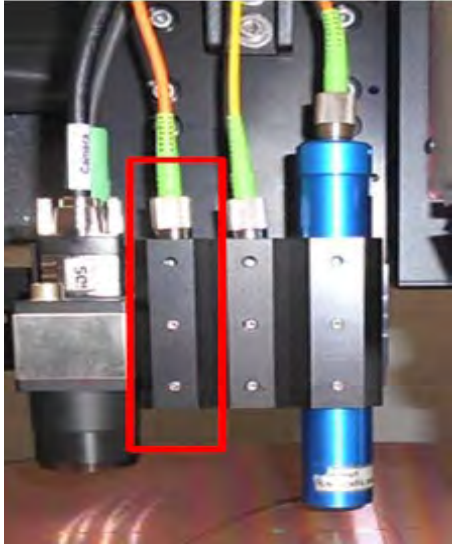
fast and reliable bonded carrier wafers thickness measurement

# Application

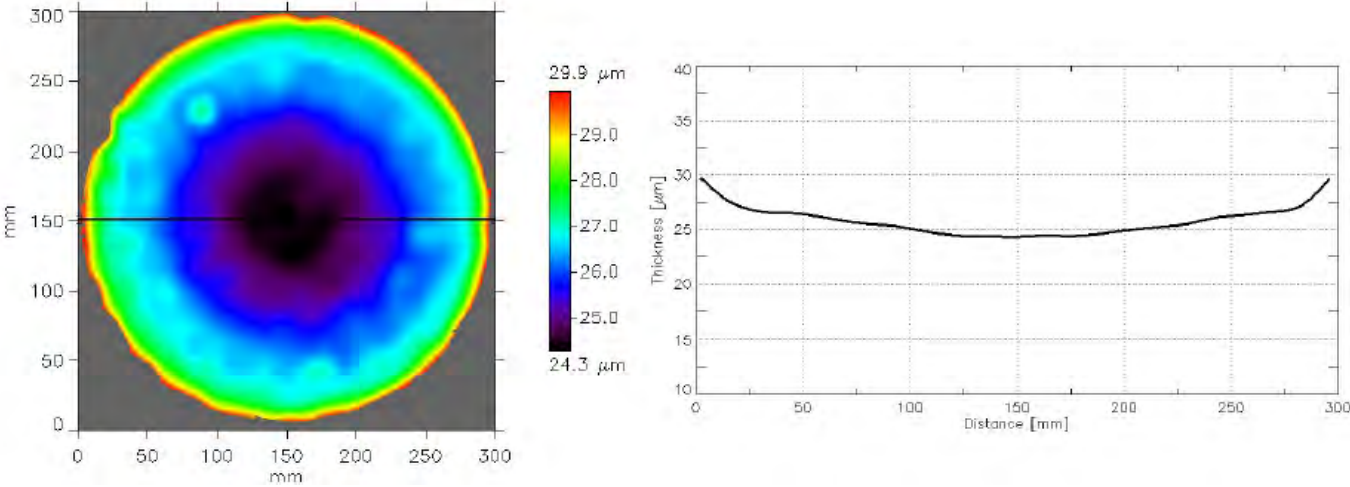
- Temporary carrier bonding



dedicated sensor:  
IRT 80



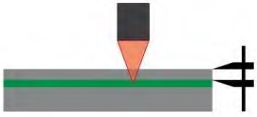
device wafer



fast and reliable bonded device wafers thickness measurement

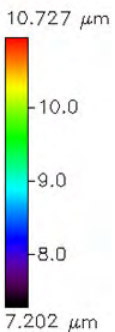
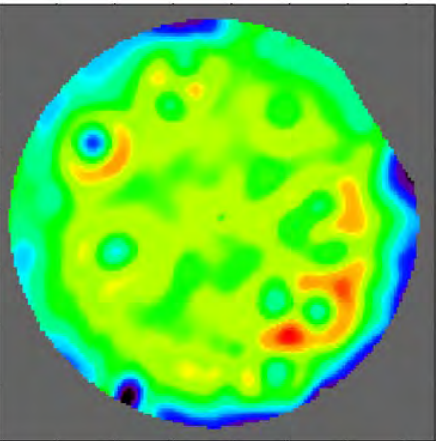
# Application

- thickness measurement of buried glue



Temporary carrier bonding

Glue thickness

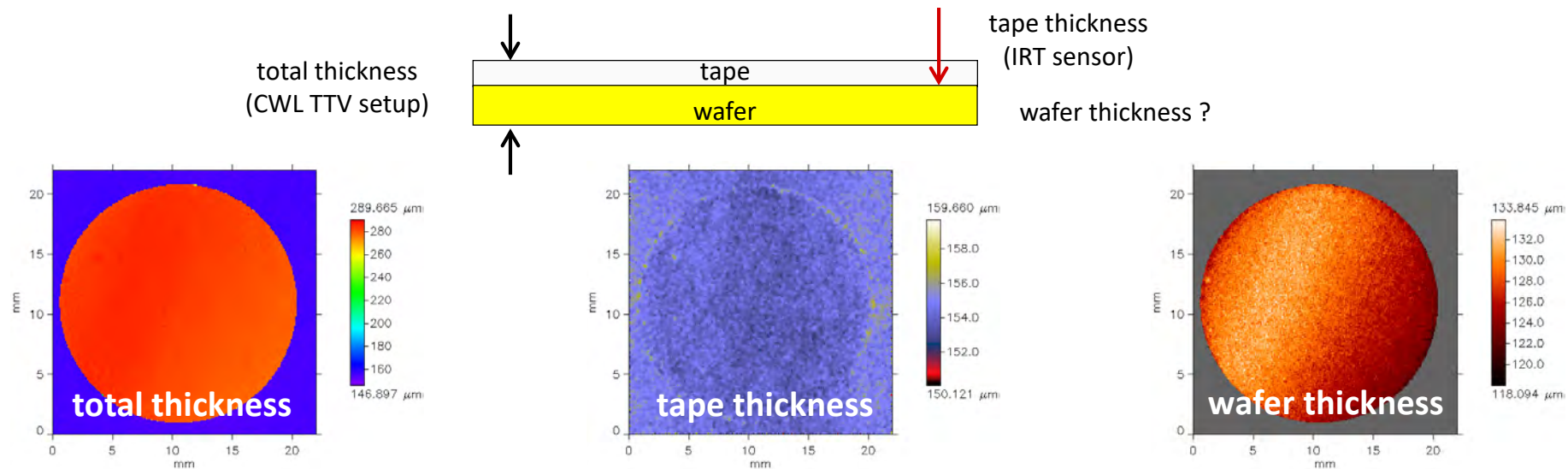


average thickness[um]	min. thickness [um]	max. thickness [um]
9.48	7.2	10.73

glue thickness measurement over full wafer possible

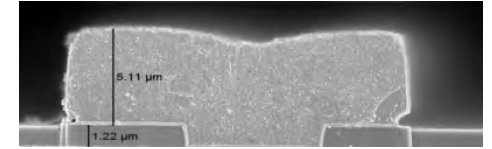
# Hybrid metrology - Wafer + tape thickness

- total thickness measurement: wafer+tape (CWL TTV setup)
- measurement of tape thickness (IRT sensor)
- evaluation of wafer thickness  
→ hybrid metrology: total thickness – tape thickness = wafer thickness

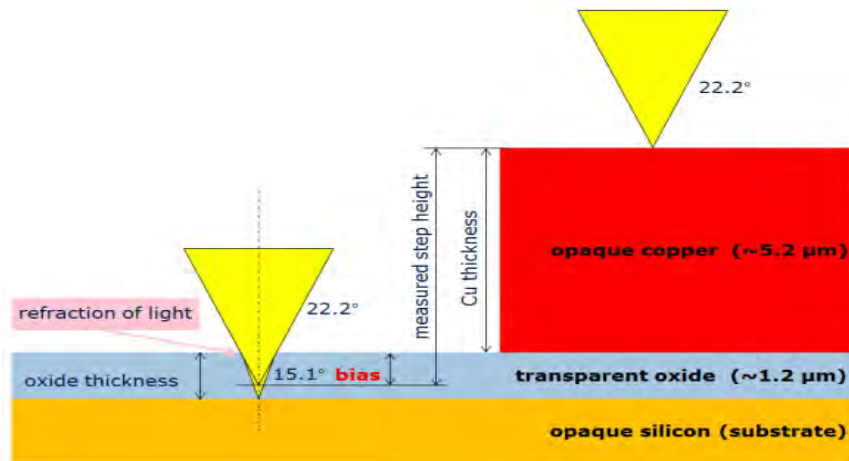


# Hybrid metrology

- Step height of metal pads on transparent layer

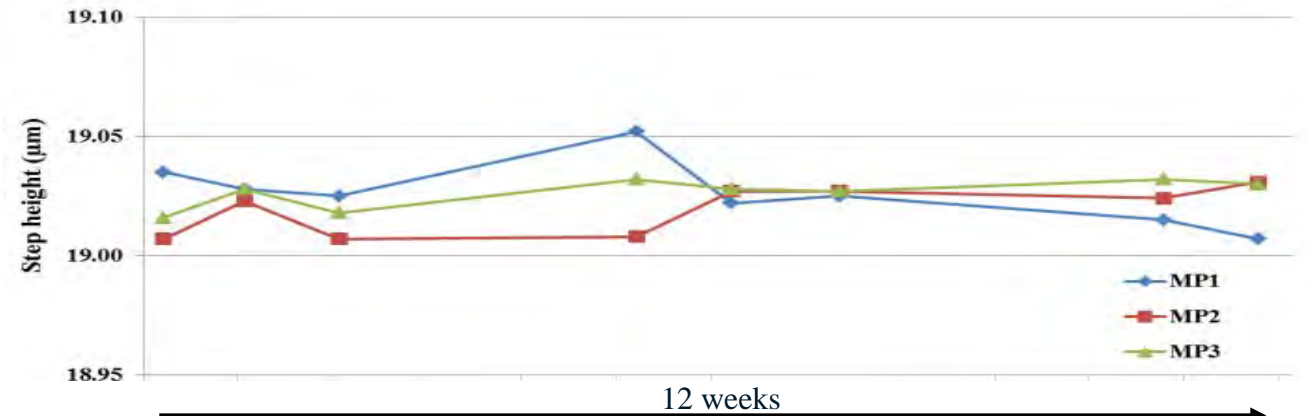


evaluation of step height and oxide thickness



dynamic repeatability tests for 12 weeks:

$$\sigma = 9 \text{ nm (0.17 \%)}$$



ASMC2015: Optical step height and trench depth measurement, F.Heider et al. Infineon/FRT

# Hybrid metrology

- Topography and thickness measurement of transparent layers

- combination of various measurement tasks using different sensors to run fully automated in one task

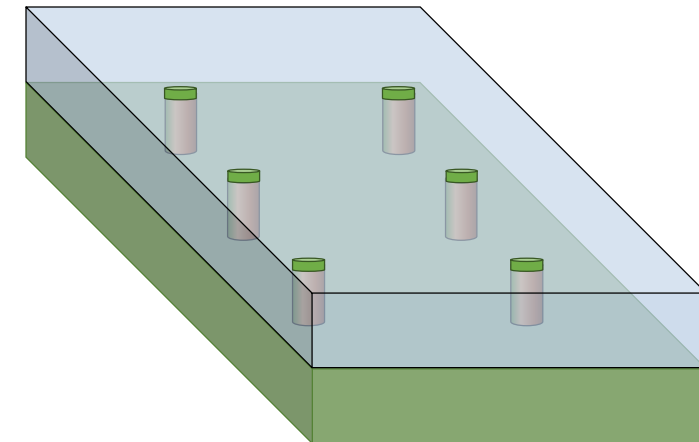
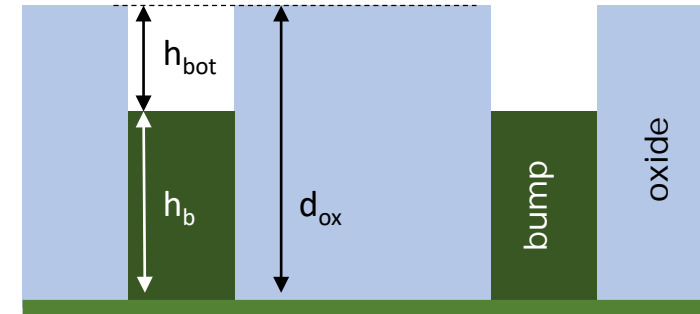
- measurements

CFM → bump to oxide recess:  $h_{\text{bot}}$

FTR → film thickness:  $d_{\text{ox}}$

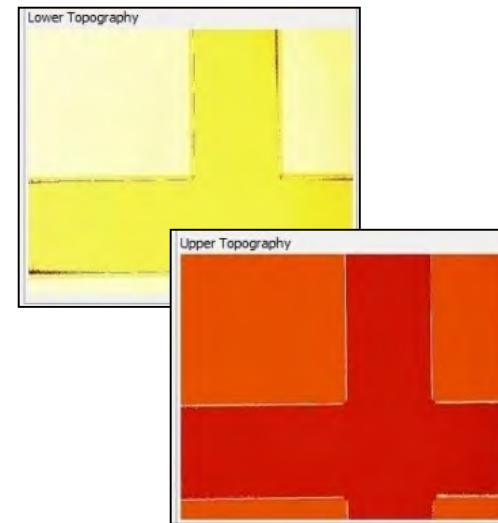
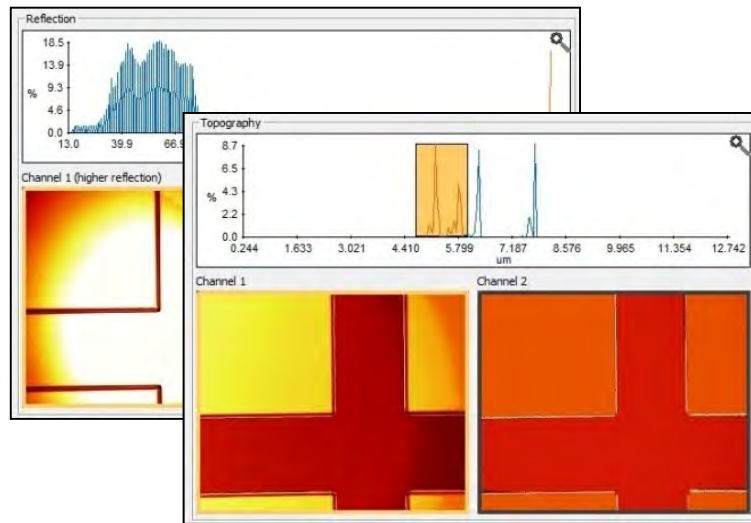
- hybrid metrology

$$\text{bump height: } h_b = d_{\text{ox}} - h_{\text{bot}}$$



# Hybrid metrology

- Topography and thickness measurement of transparent layers
  - distinguishing reflections coming from different surface layers
    - topography measurement of a poorly reflective transparent layer, ignoring the signal of the underlying highly reflective substrate
    - direct thickness determination of a transparent layer with known refractive index



# Thank you for your attention



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